

Title (en)  
METHOD FOR MANUFACTURING A MONOCRYSTALLINE PIEZOELECTRIC LAYER, AND MICROELECTRONIC, PHOTONIC, OR OPTICAL DEVICE INCLUDING SUCH A LAYER

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINER MONOKRISTALLINEN PIEZOELEKTRISCHEN SCHICHT UND MIKROELEKTRONISCHE, FOTONISCHE ODER OPTISCHE VORRICHTUNG MIT SOLCH EINER SCHICHT

Title (fr)  
PROCEDE DE FABRICATION D'UNE COUCHE PIEZOELECTRIQUE MONOCRISTALLINE ET DISPOSITIF MICROELECTRONIQUE, PHOTONIQUE OU OPTIQUE COMPRENANT UNE TELLE COUCHE

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Application  
**EP 16819091 A 20161221**

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Abstract (en)  
[origin: WO2017109005A1] The invention relates to a method for manufacturing a monocrystalline piezoelectric material layer (10). Said method is characterized in that it includes: providing a donor substrate (100) made of said piezoelectric material, providing a receiving substrate (110), transferring a so-called "seed layer" (102) of said donor substrate (100) onto the receiving substrate (110), and using epitaxy of the piezoelectric material on the seed layer (102) until the desired thickness is obtained for the monocrystalline piezoelectric layer (10).

IPC 8 full level  
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CPC (source: CN EP KR US)  
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Designated contracting state (EPC)  
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